

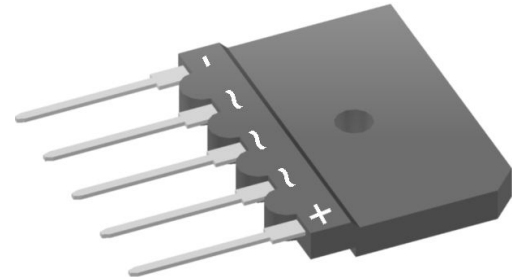
Standard Rectifier

3~ Rectifier	
V_{RRM}	= 1200 V
I_{DAV}	= 40 A
I_{FSM}	= 370 A

3~ Rectifier Bridge

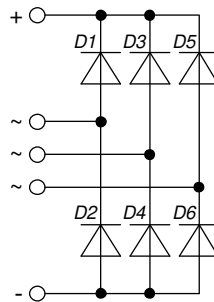
Part number

GUO40-12NO1



Backside: isolated

 E72873



Features / Advantages:

- Low forward voltage drop
- Planar passivated chips
- Easy to mount with one screw
- Space and weight savings

Applications:

- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: GUPF

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Base plate: Plastic overmolded tab
- Reduced weight

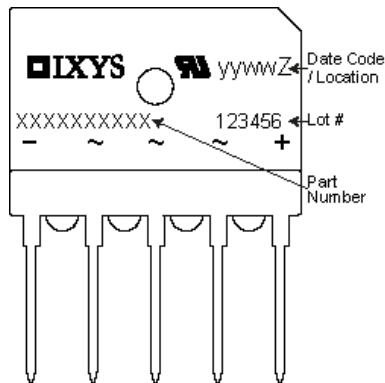
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					1300	V
V_{RRM}	max. repetitive reverse blocking voltage					1200	V
I_R	reverse current	$V_R = 1200$ V		$T_{VJ} = 25^\circ\text{C}$		40	μA
		$V_R = 1200$ V		$T_{VJ} = 150^\circ\text{C}$		1.5	mA
V_F	forward voltage drop	$I_F = 10$ A		$T_{VJ} = 25^\circ\text{C}$		1.06	V
		$I_F = 30$ A				1.28	V
		$I_F = 10$ A		$T_{VJ} = 150^\circ\text{C}$		0.92	V
		$I_F = 30$ A				1.23	V
I_{DAV}	bridge output current	$T_C = 90^\circ\text{C}$	rectangular	$T_{VJ} = 175^\circ\text{C}$		40	A
			$d = \frac{1}{3}$				
V_{FO}	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^\circ\text{C}$		0.74	V
r_F	slope resistance					16.3	m Ω
R_{thJC}	thermal resistance junction to case					4.3	K/W
R_{thCH}	thermal resistance case to heatsink				0.5		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		35	W
I_{FSM}	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		370	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		400	A
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		315	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		340	A
I^2t	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		685	A ² s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		665	A ² s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		495	A ² s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		480	A ² s
C_J	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^\circ\text{C}$		10	pF



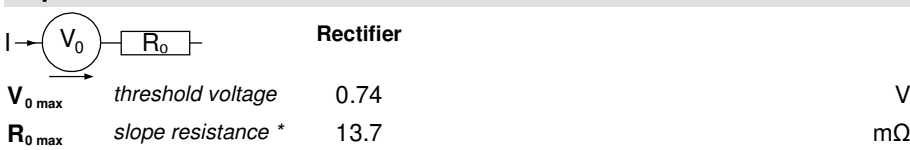
Package GUPF		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			70	A
T_{VJ}	virtual junction temperature		-40		175	°C
T_{op}	operation temperature		-40		150	°C
T_{stg}	storage temperature		-40		150	°C
Weight				8.5		g
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	6.7	5.4		mm
$d_{Spb/Apb}$		terminal to backside	10.0	8.0		mm
V_{ISOL}	isolation voltage	t = 1 second		2500		V
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	2100		V
R_{thJA}	thermal resistance junction to ambient			50		K/W



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	GUO40-12NO1	GUO40-12NO1	Tube	14	514892

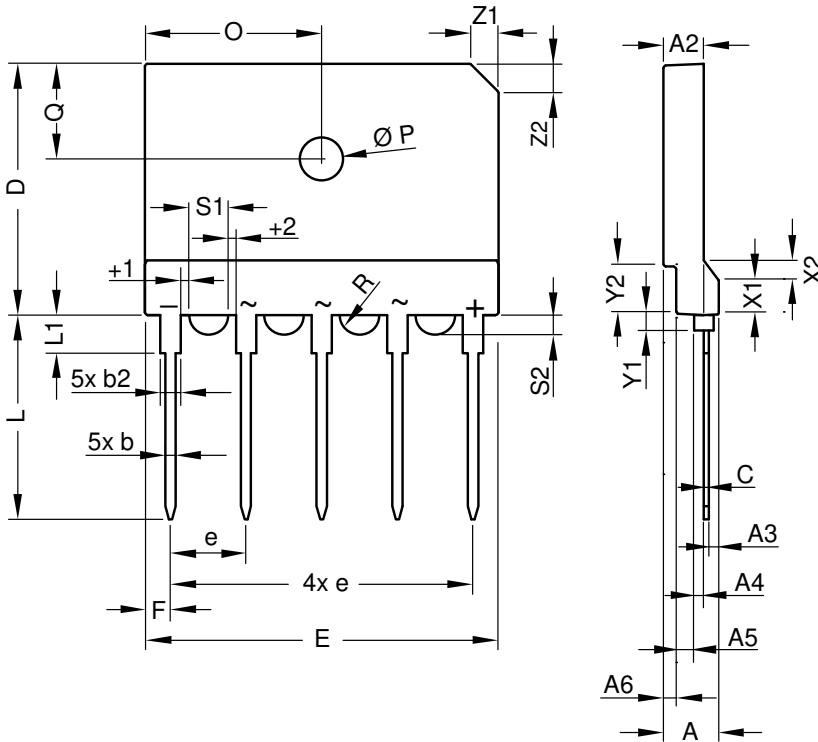
Similar Part	Package	Voltage class
DNA40U2200GU	GUPF	2200
DMA40U1800GU	GUPF	1800
GUO40-16NO1	GUPF	1600
GUO40-08NO1	GUPF	800

Equivalent Circuits for Simulation * on die level $T_{VJ} = 175^{\circ}C$

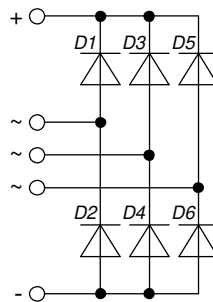




Outlines GUPF



Dim.	Millimeter			Inches		
	min	typ.	max	min	typ.	max
A	5.40	5.50	5.60	0.213	0.217	0.221
A2	3.90	4.00	4.10	0.154	0.158	0.162
A3	0.95	1.00	1.10	0.037	0.039	0.043
A4	0.95	1.00	1.05	0.037	0.039	0.041
A5	1.60	1.70	1.80	0.063	0.067	0.071
A6	1.25	1.30	1.35	0.049	0.051	0.053
b	0.95	1.00	1.05	0.037	0.039	0.041
b2	1.95	2.00	2.05	0.077	0.079	0.081
C	0.45	0.50	0.55	0.018	0.020	0.022
D	24.80	25.00	25.20	0.977	0.985	0.993
E	34.70	35.00	35.30	1.367	1.379	1.391
e	BSC 7.50			BSC 0.296		
F	2.40	2.50	2.60	0.095	0.099	0.102
L	20.30	20.40	20.50	0.800	0.804	0.808
L1	3.70	3.75	3.80	0.146	0.148	0.150
O	17.40	17.50	17.60	0.686	0.690	0.693
$\varnothing P$	4.10	4.20	4.30	0.162	0.165	0.169
Q	9.20	9.30	9.40	0.362	0.366	0.370
$\varnothing/2 R$		1.77			0.070	
s1	3.45	3.50	3.55	0.136	0.138	0.140
s2	1.45	1.50	1.55	0.057	0.059	0.061
t1	0.95	1.00	1.05	0.037	0.039	0.041
t2	0.95	1.00	1.05	0.037	0.039	0.041
x1	3.20	3.30	3.40	0.126	0.130	0.134
x2	1.90	2.00	2.10	0.075	0.079	0.083
y1	1.60	1.65	1.70	0.063	0.065	0.067
y2	4.65	4.70	4.75	0.183	0.185	0.187
z1	2.80	2.90	3.00	0.110	0.114	0.118



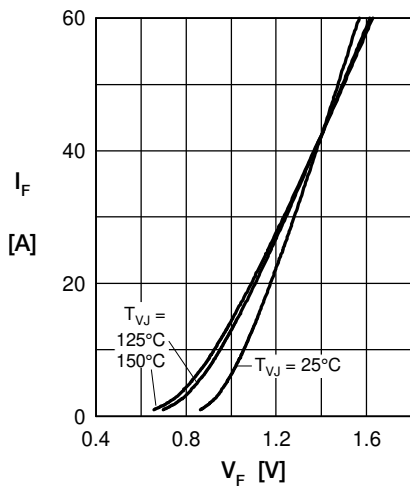
Rectifier


Fig. 1 Forward current vs. voltage drop per diode

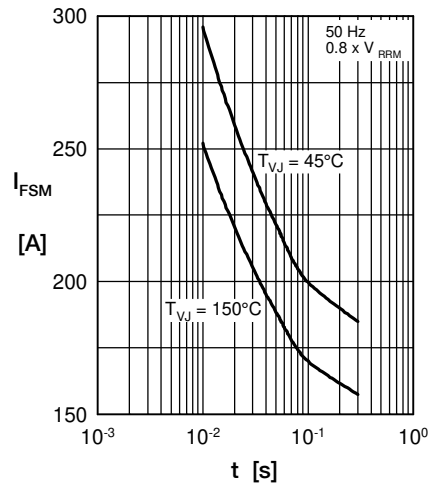


Fig. 2 Surge overload current vs. time per diode

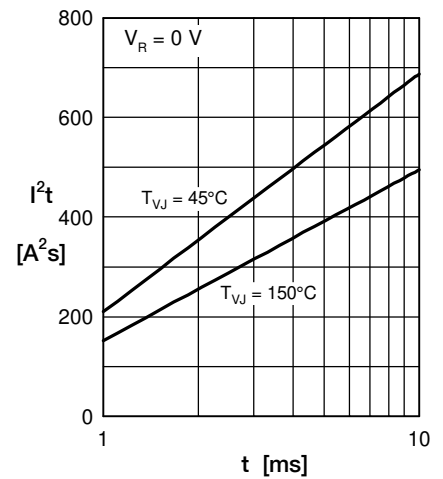
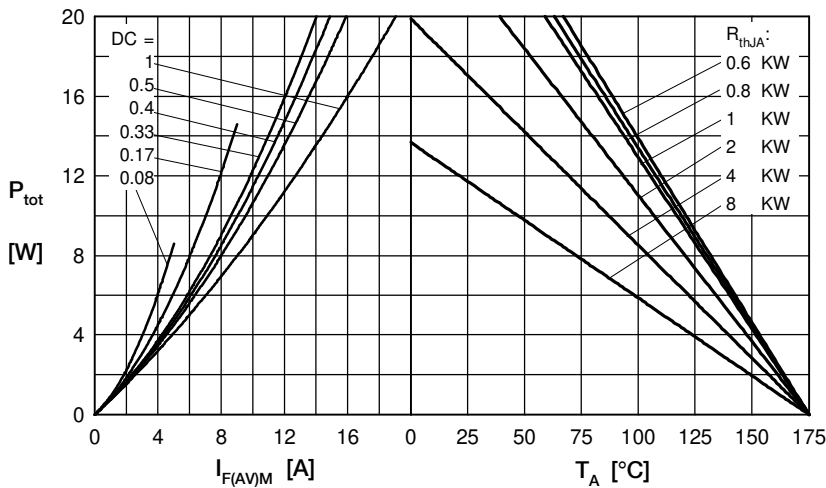

 Fig. 3 I^2t vs. time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

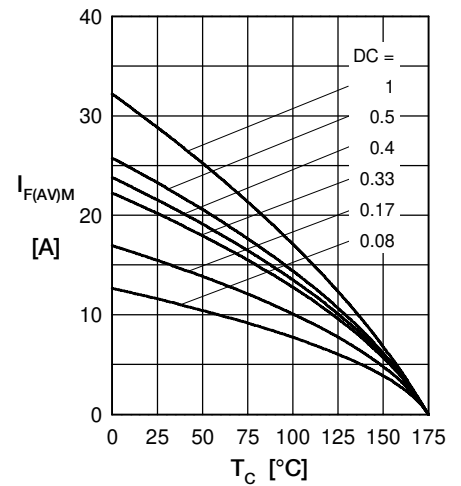


Fig. 5 Max. forward current vs. case temperature per diode

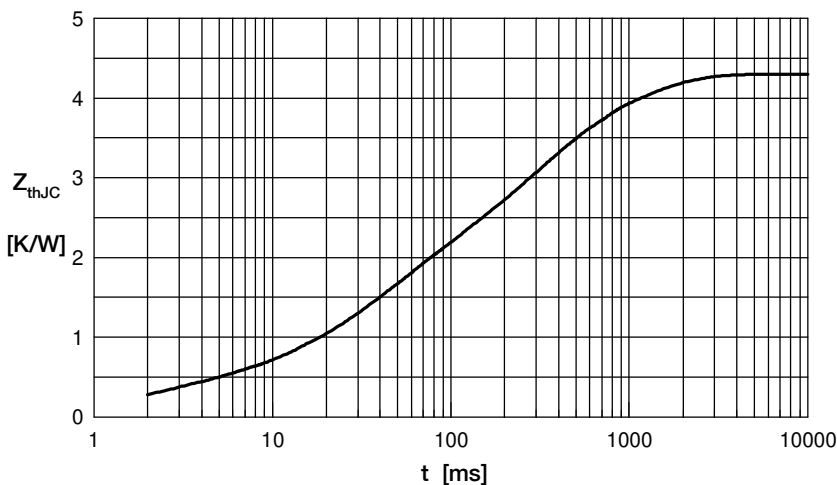


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.302	0.002
2	1.252	0.032
3	1.582	0.227
4	1.164	0.820